

Silicon NPN Power Transistors

2SC3387

DESCRIPTION

- With TO-3PN package
- High breakdown voltage
- Fast switching speed

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

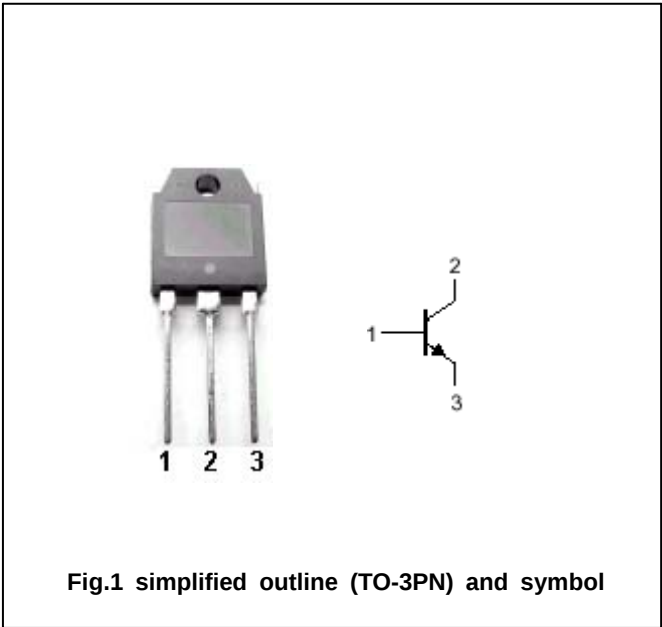


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1200	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		10	A
P _C	Collector power dissipation	T _C =25℃	50	W
T _j	Junction temperature		150	℃
T _{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA ; I_B=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A ; I_B=0.8A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A ; I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V ; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V ; I_C=0$			10	μA
h_{FE}	DC current gain	$I_C=0.3A ; V_{CE}=5V$	15			

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PACKAGE OUTLINE

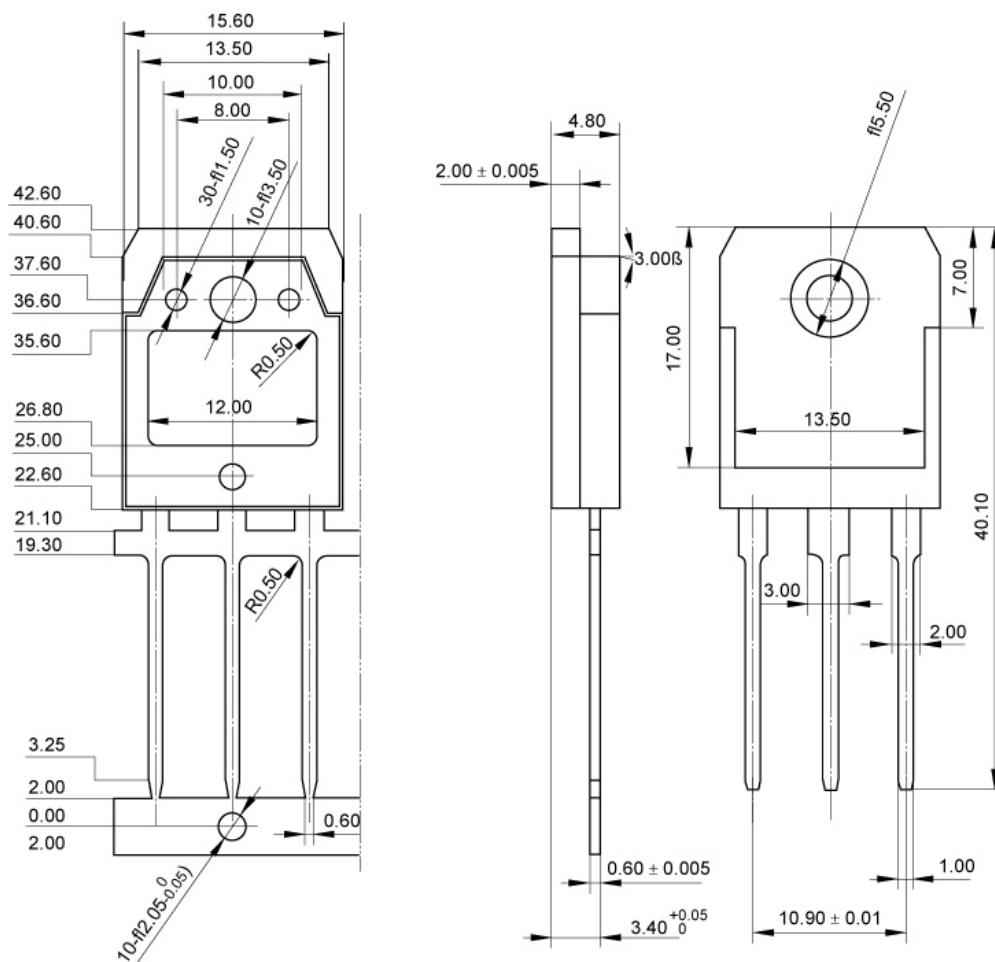


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)